

BUK7K25-40E

Dual N-channel TrenchMOS standard level FET

23 April 2013

Product data sheet

1. General description

Dual standard level N-channel MOSFET in a LPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with $V_{GS(th)} > 1\text{ V @ }175\text{ °C}$

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

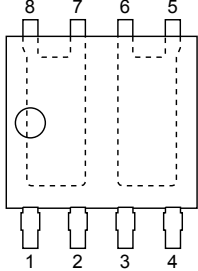
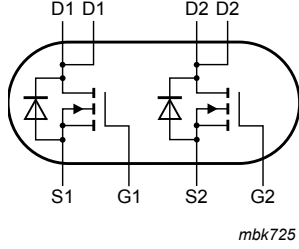
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	40	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	27	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 2}$	-	-	32	W
Static characteristics FET1 and FET2						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ °C}; \text{Fig. 12}$	-	21.25	25	mΩ
Dynamic characteristics FET1 and FET2						
Q_{GD}	gate-drain charge	$I_D = 5\text{ A}; V_{DS} = 32\text{ V}; V_{GS} = 20\text{ V}; T_j = 25\text{ °C}; \text{Fig. 14}; \text{Fig. 15}$	-	2.6	-	nC



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 LFPAK56D (SOT1205)	 mbk725
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7K25-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7K25-40E	72540E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$; $T_j \leq 175\text{ }^\circ\text{C}$	-	40	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$; $T_j \geq 25\text{ }^\circ\text{C}$; $T_j \leq 175\text{ }^\circ\text{C}$	-	40	V
V_{GS}	gate-source voltage	$T_j \leq 175\text{ }^\circ\text{C}$; DC	-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 1	-	27	A
		$T_{mb} = 100\text{ }^\circ\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 1	-	19	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^\circ\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 4	-	107	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$; Fig. 2	-	32	W

Symbol	Parameter	Conditions		Min	Max	Unit
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{\text{sld(M)}}$	peak soldering temperature			-	260	°C
Source-drain diode FET1 and FET2						
I_S	source current	$T_{\text{mb}} = 25\text{ °C}$		-	27	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{\text{mb}} = 25\text{ °C}$		-	107	A
Avalanche Ruggedness FET1 and FET2						
$E_{\text{DS(AL)S}}$	non-repetitive drain-source avalanche energy	$I_D = 28\text{ A}$; $V_{\text{sup}} \leq 40\text{ V}$; $V_{\text{GS}} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; Fig. 3	[1] [2]	-	10	mJ

[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

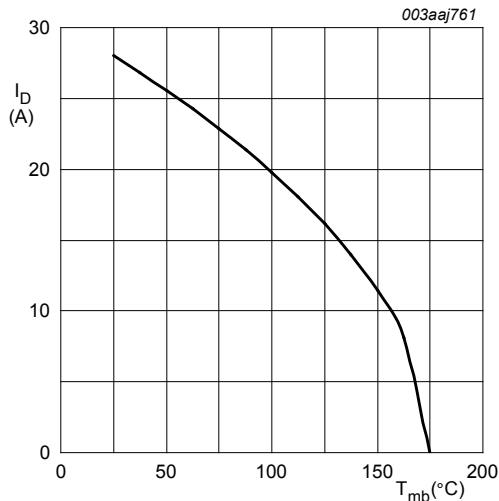


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{\text{GS}} \geq 10\text{ V}$$

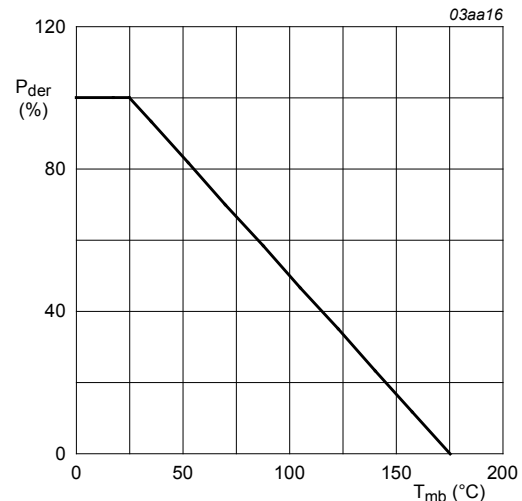


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{\text{der}} = \frac{P_{\text{tot}}}{P_{\text{tot}(25\text{ °C})}} \times 100\%$$

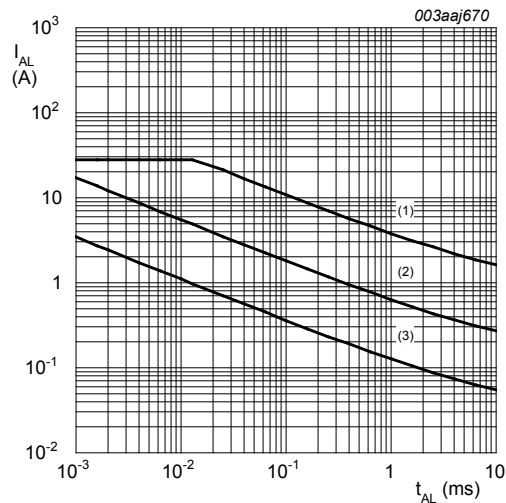


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse; $T_j = 25\text{ }^{\circ}\text{C}$.
- (2) Single-pulse; $T_j = 150\text{ }^{\circ}\text{C}$.
- (3) Repetitive.

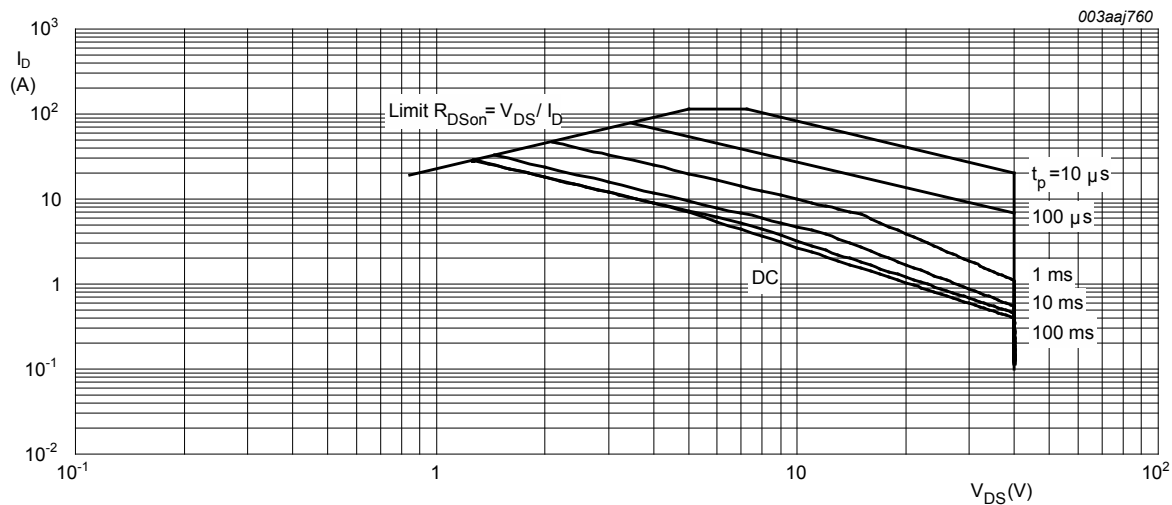


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$T_{mb} = 25\text{ }^{\circ}\text{C}$; I_{DM} is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	4.68	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

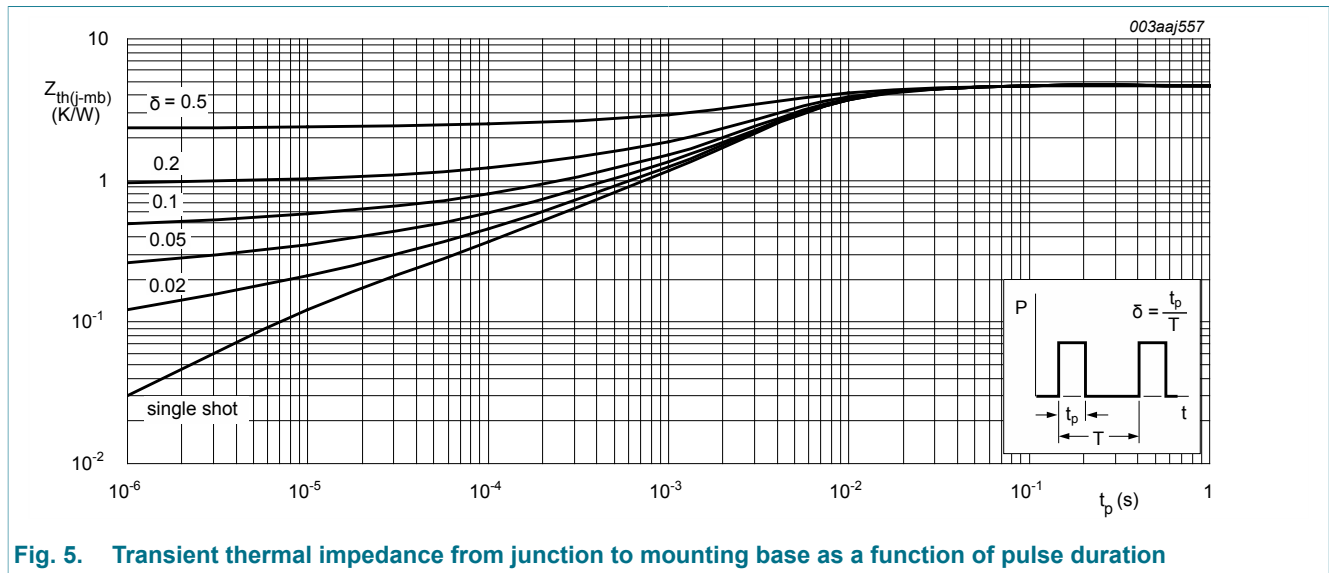


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics FET1 and FET2						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_J = -55 ^\circ C$	36	-	-	V
		$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_J = 25 ^\circ C$	40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA$; $V_{DS} = V_{GS}$; $T_J = 25 ^\circ C$; Fig. 10; Fig. 11	2.4	3	4	V
		$I_D = 1 mA$; $V_{DS} = V_{GS}$; $T_J = 175 ^\circ C$; Fig. 10; Fig. 11	1	-	-	V
		$I_D = 1 mA$; $V_{DS} = V_{GS}$; $T_J = -55 ^\circ C$; Fig. 10; Fig. 11	-	-	4.5	V
I_{DSS}	drain leakage current	$V_{DS} = 40 V$; $V_{GS} = 0 V$; $T_J = 175 ^\circ C$	-	-	500	μA
		$V_{DS} = 40 V$; $V_{GS} = 0 V$; $T_J = 25 ^\circ C$	-	0.02	1	μA
I_{GSS}	gate leakage current	$V_{GS} = -20 V$; $V_{DS} = 0 V$; $T_J = 25 ^\circ C$	-	2	100	nA
		$V_{GS} = 20 V$; $V_{DS} = 0 V$; $T_J = 25 ^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V$; $I_D = 5 A$; $T_J = 25 ^\circ C$; Fig. 12	-	21.25	25	m Ω
		$V_{GS} = 10 V$; $I_D = 5 A$; $T_J = 175 ^\circ C$; Fig. 12; Fig. 13	-	40.1	49.3	m Ω

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics FET1 and FET2						
$Q_{G(tot)}$	total gate charge	$I_D = 5\text{ A}$; $V_{DS} = 32\text{ V}$; $V_{GS} = 10\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 14 ; Fig. 15	-	7.9	-	nC
Q_{GS}	gate-source charge		-	1.5	-	nC
Q_{GD}	gate-drain charge	$I_D = 5\text{ A}$; $V_{DS} = 32\text{ V}$; $V_{GS} = 20\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 14 ; Fig. 15	-	2.6	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 25\text{ V}$; $f = 1\text{ MHz}$; $T_J = 25\text{ }^\circ\text{C}$	-	394	525	pF
C_{oss}	output capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 25\text{ V}$; $f = 1\text{ MHz}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 16	-	107	128	pF
C_{rss}	reverse transfer capacitance		-	76	104	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 32\text{ V}$; $R_L = 6.5\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $R_{G(ext)} = 5\text{ }\Omega$; $T_J = 25\text{ }^\circ\text{C}$; $I_D = 5\text{ A}$	-	4.4	-	ns
t_r	rise time		-	4.5	-	ns
$t_{d(off)}$	turn-off delay time		-	8.3	-	ns
t_f	fall time		-	5.2	-	ns
Source-drain diode FET1 and FET2						
V_{SD}	source-drain voltage	$I_S = 5\text{ A}$; $V_{GS} = 0\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 17	-	0.78	1.2	V
t_{rr}	reverse recovery time	$I_S = 5\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 20\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$	-	12.4	-	ns
Q_r	recovered charge		-	6.7	-	nC

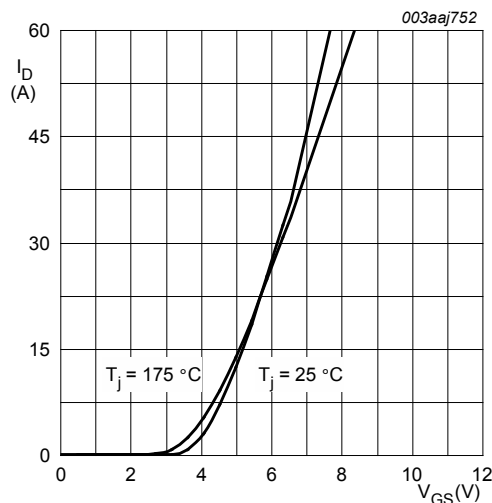


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10\text{ V}$$

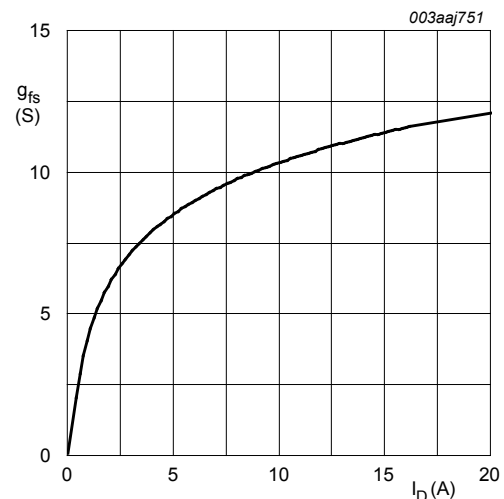


Fig. 7. Forward transconductance as a function of drain current; typical values

$$T_J = 25\text{ }^\circ\text{C}; V_{DS} = 15\text{ V}$$

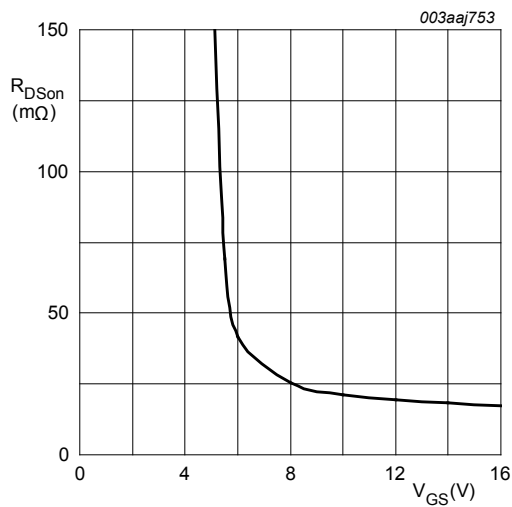


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}; I_D = 5\text{ A}$

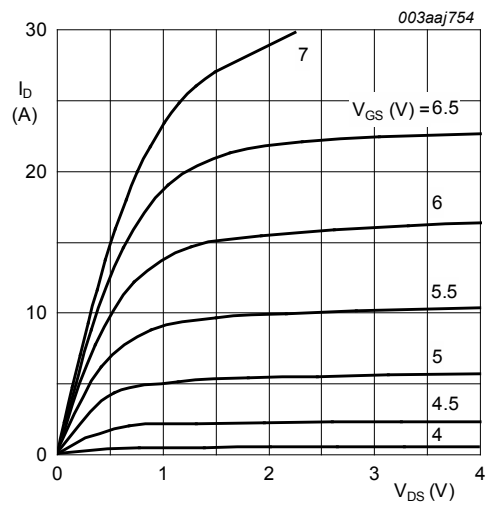


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}$

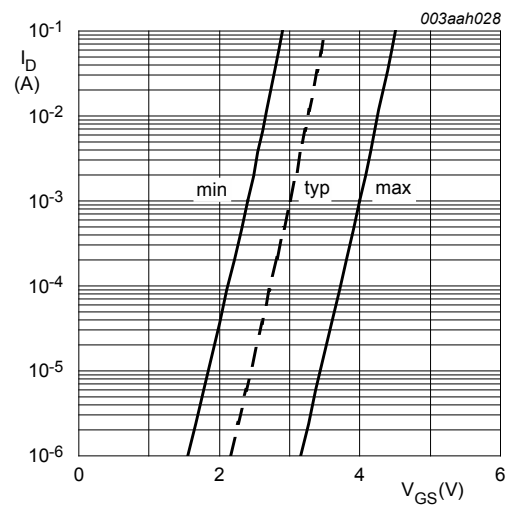


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

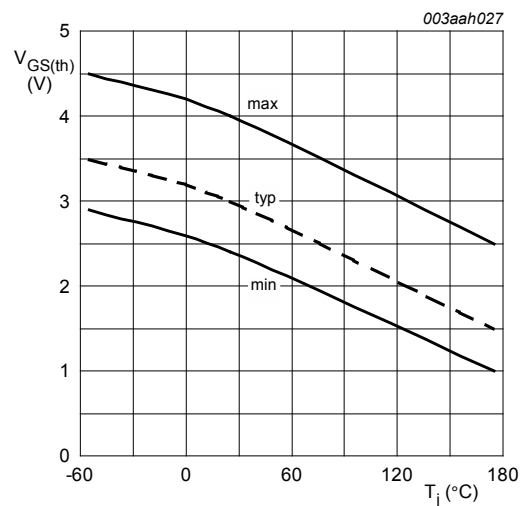


Fig. 11. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

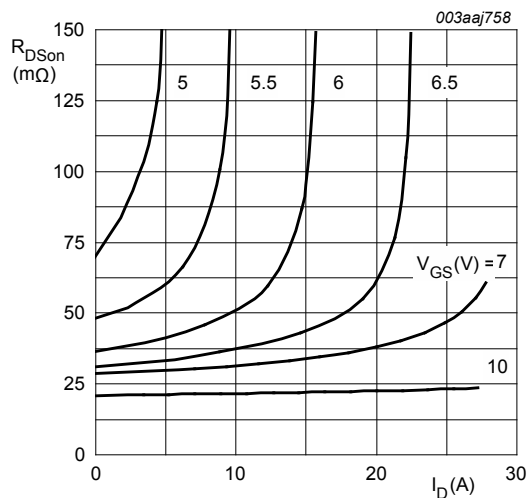


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25\text{ }^{\circ}\text{C}$

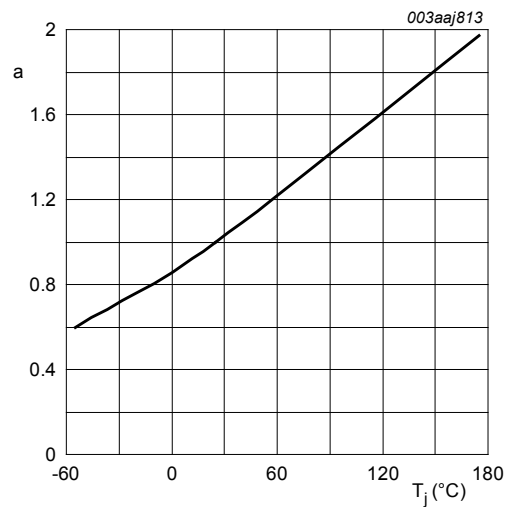


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

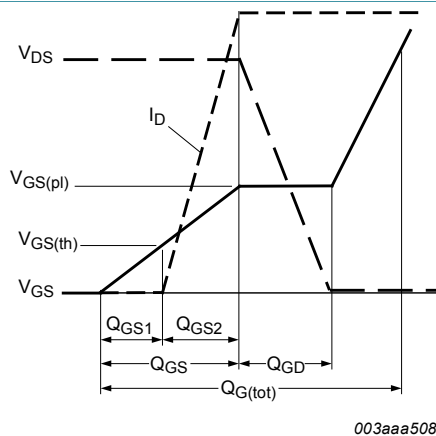


Fig. 14. Gate charge waveform definitions

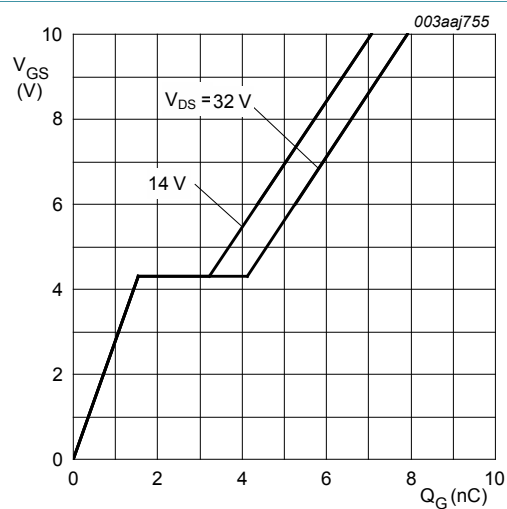


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25\text{ }^{\circ}\text{C}; I_D = 5\text{ A}$

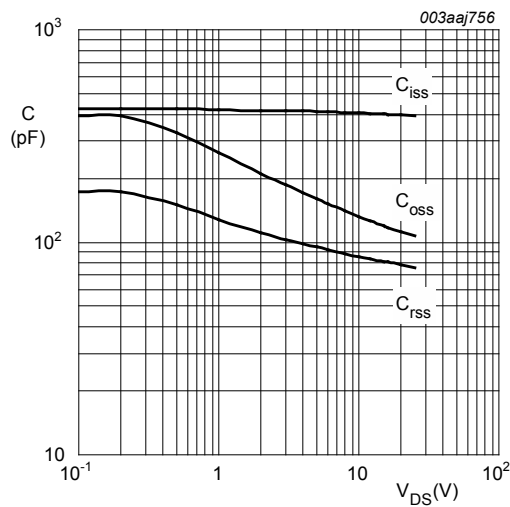


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

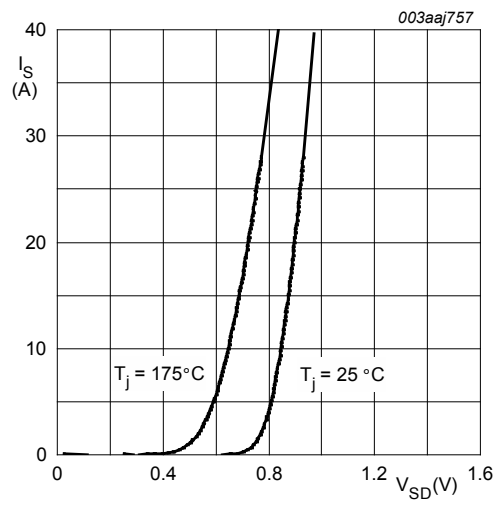


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\text{ V}$

11. Package outline

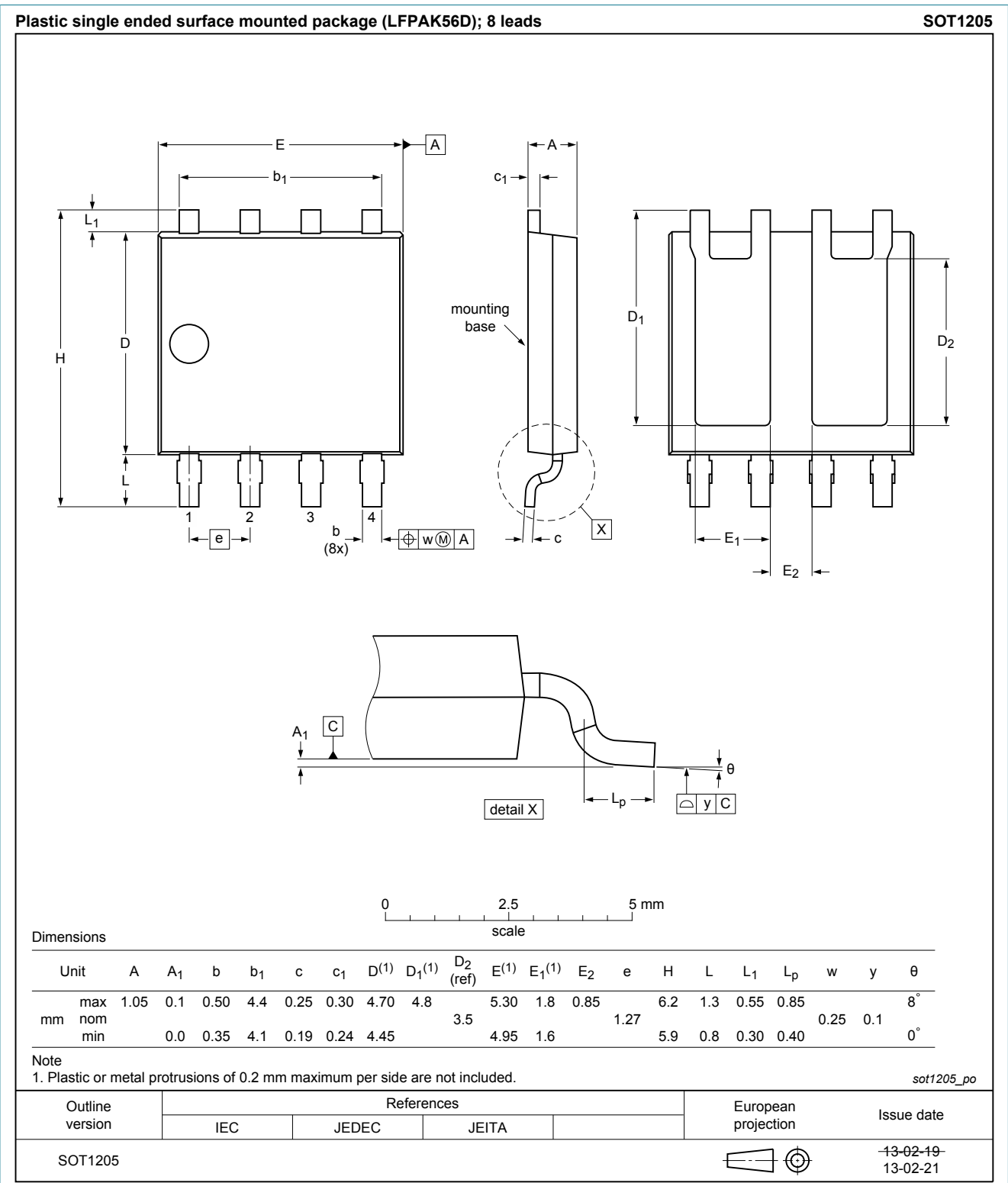


Fig. 18. Package outline LPAK56D (SOT1205)

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12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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